



Electron Transport Material for OLEDs

LET321 TFDT

Product Specifications

HOMO/LUMO	-5.21 eV / -3.00 eV
Triplet Energy	2.48 eV
Tm	347 °C
Td	364 °C
UV (in DCM)	267,375 nm
PL (in DCM)	424 nm

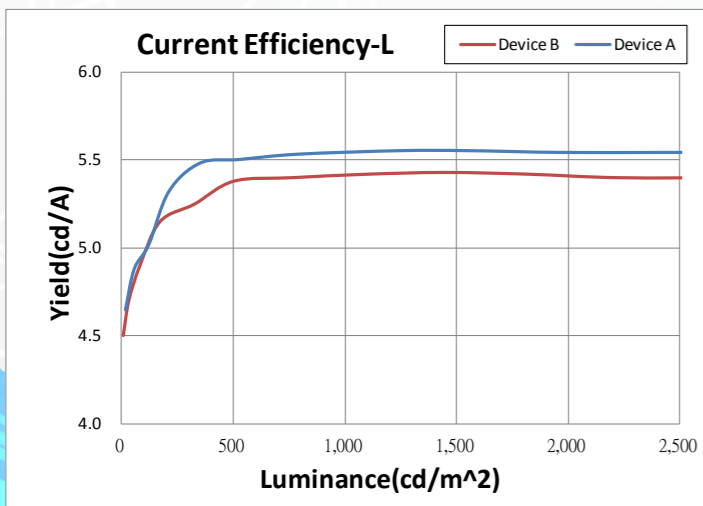
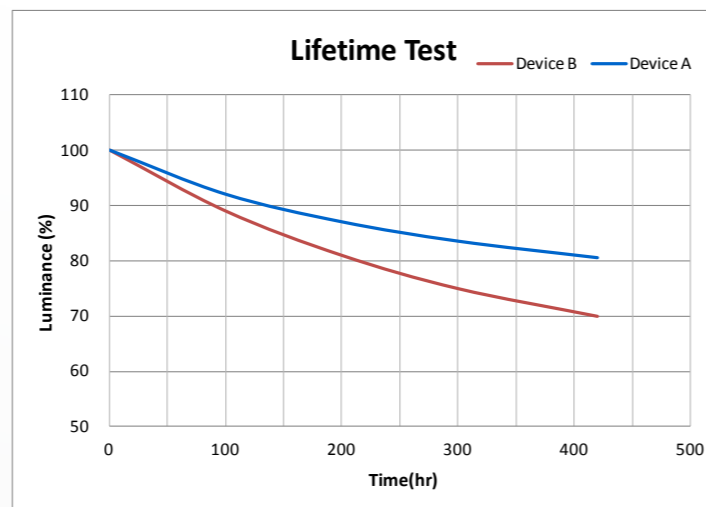
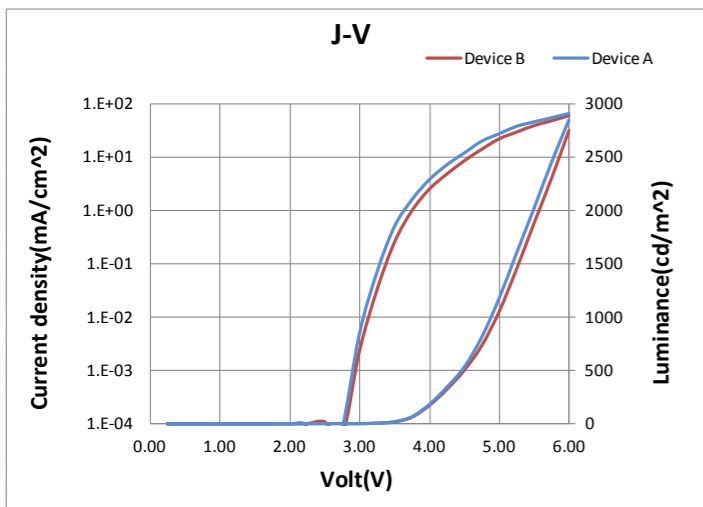
Feature

1. Unique patented material
2. Competitive price with better performance

*Suggest Deposition Temp. 175°C at 5X10⁻⁶ torr

Device Application

Device A: ITO/HIL(20nm)/HTL(130nm)/EBL(5nm)/Blue EML(25nm)/HBL(5nm)/LET321:LiQ(25nm)/LiQ(1nm)/Al(150nm)
 Device B: ITO/HIL(20nm)/HTL(130nm)/EBL(5nm)/Blue EML(25nm)/HBL(5nm)/ETL from Jp:LiQ(25nm)/LiQ(1nm)/Al(150nm)



Item	ETL from Jp	LET321
CIE x	0.14	0.14
CIE y	0.10	0.10
Volt@1000nits	5.00	5.00
LE(cd/A)	5.42	5.55
T80(hr)@40mA/cm ²	215	420



Phosphorescent Host material for OLEDs

LPH604

Product Specifications

HOMO/LUMO	-5.15 eV / -1.96 eV
Triplet Energy	2.64 eV
Tm	351 °C
Td	397 °C
UV (in DCM)	261, 378 nm
PL (in DCM)	422 nm

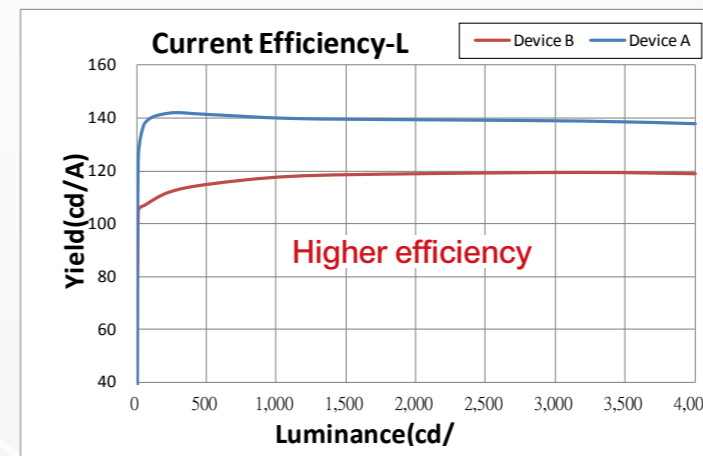
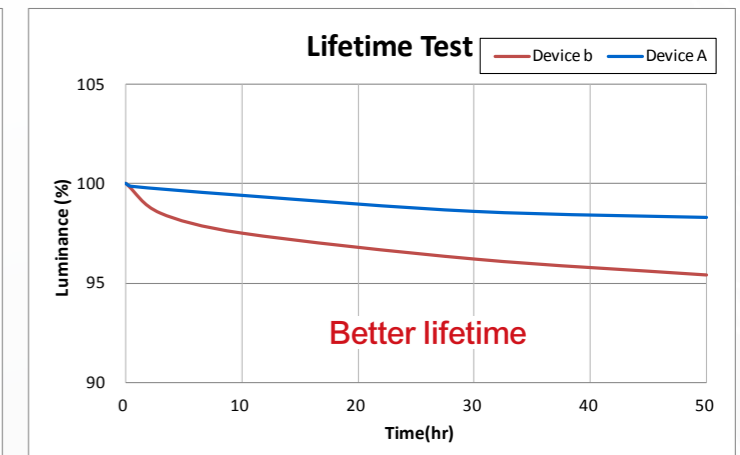
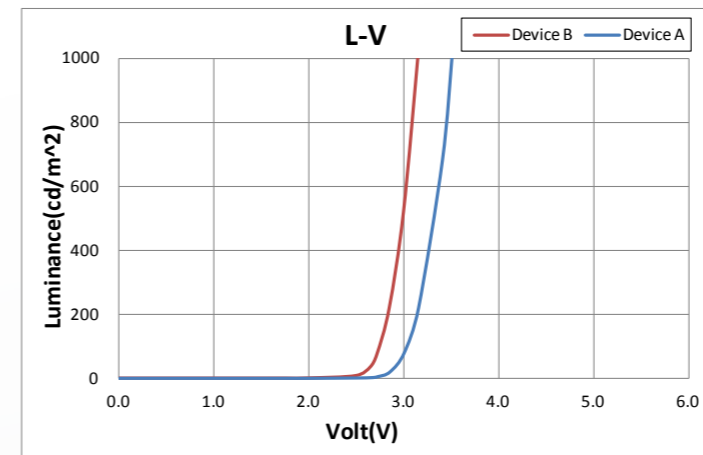
Feature

1. Unique patented material
2. Competitive price with better performance

*Suggest Deposition Temp. 214°C at 5X10⁻⁶ torr

Device Application

Device A: Anode/HIL(20nm)/HTL(130nm)/EBL(5nm)/10%GD+ LPH604 (30nm)/ETL-2(25nm)/ETL-1(1nm)/Thin cathode(150nm)
 Device B: Anode/HIL(20nm)/HTL(130nm)/EBL(5nm)/10%GD+ Premix Host(30nm)/ETL-2(25nm)/ETL-1(1nm)/Thin cathode(150nm)



Item	Premix Host	LPH604
CIE x	0.34	0.36
CIE y	0.65	0.63
Volt@1000nits	3.1	3.5
LE(cd/A)	118	140
T80(hr)@40mA/cm ²	5	50